

# Peter J Wellmann

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/3439302/publications.pdf>

Version: 2024-02-01

150  
papers

1,439  
citations

393982

19  
h-index

454577

30  
g-index

173  
all docs

173  
docs citations

173  
times ranked

1235  
citing authors

#	ARTICLE	IF	CITATIONS
1	Application of optical absorbance for the investigation of electronic and structural properties of sol-gel processed TiO <sub>2</sub> films. Thin Solid Films, 2008, 516, 7256-7259.	0.8	97
2	Review of SiC crystal growth technology. Semiconductor Science and Technology, 2018, 33, 103001.	1.0	82
3	Electrical, optical and morphological properties of nanoparticle indium-tin-oxide layers. Thin Solid Films, 2007, 515, 8567-8572.	0.8	62
4	Power Electronic Semiconductor Materials for Automotive and Energy Saving Applications – SiC, GaN, Ga <sub>2</sub> O <sub>3</sub> , and Diamond. Zeitschrift Fur Anorganische Und Allgemeine Chemie, 2017, 643, 1312-1322.	0.6	60
5	Advances in wide bandgap SiC for optoelectronics. European Physical Journal B, 2014, 87, 1.	0.6	58
6	Ammonothermal Synthesis of Earth-Abundant Nitride Semiconductors ZnSiN <sub>2</sub> and ZnGeN <sub>2</sub> and Dissolution Monitoring by In Situ X-ray Imaging. Chemistry - A European Journal, 2017, 23, 12275-12282.	1.7	51
7	Cubic silicon carbide as a potential photovoltaic material. Solar Energy Materials and Solar Cells, 2016, 145, 104-108.	3.0	41
8	Single Domain 3C-SiC Growth on Off-Oriented 4H-SiC Substrates. Crystal Growth and Design, 2015, 15, 2940-2947.	1.4	38
9	SiC single crystal growth by a modified physical vapor transport technique. Journal of Crystal Growth, 2005, 275, e555-e560.	0.7	35
10	New Approaches and Understandings in the Growth of Cubic Silicon Carbide. Materials, 2021, 14, 5348.	1.3	34
11	Growth of SiC bulk crystals for application in power electronic devices – process design, 2D and 3D X-ray in situ visualization and advanced doping. Crystal Research and Technology, 2015, 50, 2-9.	0.6	33
12	Conductance Enhancement Mechanisms of Printable Nanoparticulate Indium Tin Oxide (ITO) Layers for Application in Organic Electronic Devices. Advanced Engineering Materials, 2009, 11, 295-301.	1.6	29
13	Intermetallic compounds dynamic formation during annealing of stacked elemental layers and its influences on the crystallization of Cu <sub>2</sub> ZnSnSe <sub>4</sub> films. Materials Chemistry and Physics, 2013, 142, 311-317.	2.0	28
14	Conductivity and adhesion enhancement in low-temperature processed indium tin oxide/polymer nanocomposites. Thin Solid Films, 2010, 518, 2910-2915.	0.8	24
15	In situ visualization of SiC physical vapor transport crystal growth. Journal of Crystal Growth, 2005, 275, e1807-e1812.	0.7	23
16	Bulk growth of SiC – review on advances of SiC vapor growth for improved doping and systematic study on dislocation evolution. Physica Status Solidi (B): Basic Research, 2008, 245, 1239-1256.	0.7	23
17	Nucleation Control of Cubic Silicon Carbide on 6H- Substrates. Crystal Growth and Design, 2012, 12, 197-204.	1.4	23
18	Tuning the emission colour by manipulating terbium-terbium interactions: Terbium doped aluminum nitride as an example system. Journal of Applied Physics, 2013, 114, .	1.1	23

#	ARTICLE	IF	CITATIONS
19	Determination of GaN solubility in supercritical ammonia with NH <sub>4</sub> F and NH <sub>4</sub> Cl mineralizer by in situ x-ray imaging of crystal dissolution. <i>Journal of Crystal Growth</i> , 2015, 418, 64-69.	0.7	21
20	Epitaxial Metal Halide Perovskites by Inkjet Printing on Various Substrates. <i>Advanced Functional Materials</i> , 2020, 30, 2004612.	7.8	21
21	Stability Criteria for 4H-SiC Bulk Growth. <i>Materials Science Forum</i> , 2001, 353-356, 25-28.	0.3	20
22	Numerical Simulation of Thermal Stress Formation During PVT-Growth of SiC Bulk Crystals. <i>Materials Science Forum</i> , 2001, 353-356, 65-68.	0.3	20
23	Broadband and omnidirectional light harvesting enhancement of fluorescent SiC. <i>Optics Express</i> , 2012, 20, 7575.	1.7	17
24	Formation of Cu <sub>2</sub> SnSe <sub>3</sub> from stacked elemental layers investigated by combined in situ X-ray diffraction and differential scanning calorimetry techniques. <i>Journal of Alloys and Compounds</i> , 2014, 588, 254-258.	2.8	17
25	Low-temperature processing of transparent conductive indium tin oxide nanocomposites using polyvinyl derivatives. <i>Thin Solid Films</i> , 2011, 520, 1341-1347.	0.8	16
26	Investigation of a PVT SiC-Growth Set-up Modified by an Additional Gas Flow. <i>Materials Science Forum</i> , 2001, 353-356, 33-36.	0.3	15
27	Analysis of the Basal Plane Dislocation Density and Thermomechanical Stress during 100 mm PVT Growth of 4H-SiC. <i>Materials</i> , 2019, 12, 2207.	1.3	15
28	High Al-Doping of SiC Using a Modified PVT (M-PVT) Growth Set-Up. <i>Materials Science Forum</i> , 2005, 483-485, 31-34.	0.3	14
29	Ceramic liner technology for ammoniac synthesis. <i>Journal of Supercritical Fluids</i> , 2015, 99, 76-87.	1.6	14
30	Quantitative Study of the Role of Supersaturation during Sublimation Growth on the Yield of 50 mm 3C-SiC. <i>Materials Science Forum</i> , 0, 821-823, 77-80.	0.3	14
31	Determination of dislocation density in MOVPE grown GaN layers using KOH defect etching. <i>Journal of Crystal Growth</i> , 2008, 310, 955-958.	0.7	13
32	Growth of Large-Area, Stress-Free, and Bulk-Like 3C-SiC (100) Using 3C-SiC-on-Si in Vapor Phase Growth. <i>Materials</i> , 2019, 12, 2179.	1.3	13
33	Optimization of growth parameters for growth of high quality heteroepitaxial 3C-SiC films at 1200°C. <i>Thin Solid Films</i> , 2015, 577, 88-93.	0.8	12
34	Chemical stability of carbon-based inorganic materials for in situ x-ray investigations of ammonothermal crystal growth of nitrides. <i>Journal of Crystal Growth</i> , 2016, 456, 33-42.	0.7	11
35	Solubility and dissolution kinetics of GaN in supercritical ammonia in presence of ammoniac and ammonobasic mineralizers. <i>Journal of Crystal Growth</i> , 2017, 479, 59-66.	0.7	11
36	Impact of Mechanical Stress and Nitrogen Doping on the Defect Distribution in the Initial Stage of the 4H-SiC PVT Growth Process. <i>Materials</i> , 2022, 15, 1897.	1.3	11

#	ARTICLE	IF	CITATIONS
37	Study of Boron Incorporation During PVT Growth of p-type SiC Crystals. Materials Science Forum, 2001, 353-356, 49-52.	0.3	10
38	Observation of Lattice Plane Bending during SiC PVT Bulk Growth Using <i>in Situ</i> High Energy X-Ray Diffraction. Materials Science Forum, 0, 645-648, 29-32.	0.3	10
39	Fabrication, charge carrier transport, and application of printable nanocomposites based on indium tin oxide nanoparticles and conducting polymer 3,4-ethylenedioxythiophene/polystyrene sulfonic acid. Journal of Applied Physics, 2011, 110, 104301.	1.1	10
40	Impact of Varying Parameters on the Temperature Gradients in 100Åmm Silicon Carbide Bulk Growth in a Computer Simulation Validated by Experimental Results. Crystal Research and Technology, 2020, 55, 1900121.	0.6	10
41	Influence of the growth interface shape on the defect characteristics in the facet region of 4H-SiC single crystals. Journal of Crystal Growth, 2020, 532, 125436.	0.7	10
42	Analysis of Graphitization during Physical Vapor Transport Growth of Silicon Carbide. Materials Science Forum, 2004, 457-460, 55-58.	0.3	9
43	Development of a KOH Defect Etching Furnace with Absolute In-Situ Temperature Measurement Capability. Materials Science Forum, 2005, 483-485, 283-286.	0.3	9
44	Modified Physical Vapor Transport Growth of SiC - Control of Gas Phase Composition for Improved Process Conditions. Materials Science Forum, 2005, 483-485, 25-30.	0.3	9
45	On the importance of dislocation flow in continuum plasticity models for semiconductor materials. Journal of Crystal Growth, 2020, 532, 125414.	0.7	9
46	Polycrystalline SiC as Source Material for the Growth of Fluorescent SiC Layers. Materials Science Forum, 2013, 740-742, 39-42.	0.3	8
47	The search for new materials and the role of novel processing routes. Discover Materials, 2021, 1, 14.	1.0	8
48	Investigation of Mass Transport during SiC PVT Growth Using Digital X-Ray Imaging, <sup>13</sup> C Labeling of Source Material and Numerical Modeling. Materials Science Forum, 2003, 433-436, 9-12.	0.3	7
49	Results of SIMS, LTPL and Temperature-Dependent Hall Effect Measurements Performed on Al-Doped $\hat{\pm}$ -SiC Substrates Grown by the M-PVT Method. Materials Science Forum, 2006, 527-529, 633-636.	0.3	7
50	Cathodoluminescence characterization of organic semiconductor materials for light emitting device applications. Journal of Applied Physics, 2007, 101, 113704.	1.1	7
51	Synthesis of In <sub>2</sub> Se <sub>3</sub> and Cu <sub>2-x</sub> Se Micro- and Nanoparticles with Microwave-Assisted Solvothermal and Aqueous Redox Reactions for the Preparation and Stabilization of Printable Precursors for a CuInSe <sub>2</sub> Solar Cell Absorber Layer. Energy Procedia, 2015, 84, 62-70.	1.8	7
52	Influence of Morphological Changes in a Source Material on the Growth Interface of 4H-SiC Single Crystals. Materials, 2019, 12, 2591.	1.3	7
53	Flow Stability, Convective Heat Transfer and Chemical Reactions in Ammonothermal Autoclaves – Insights by In Situ Measurements of Fluid Temperatures. Crystals, 2020, 10, 723.	1.0	7
54	Growth Rate Control in SiC-Physical Vapor Transport Method Through Heat Transfer Modeling and Non-Stationary Process Conditions. Materials Science Forum, 2000, 338-342, 39-42.	0.3	6

#	ARTICLE	IF	CITATIONS
55	Absorption Measurements and Doping Level Evaluation in n-Type and p-Type 4H-SiC and 6H-SiC. Materials Science Forum, 2001, 353-356, 397-400.	0.3	6
56	In Situ X-Ray Measurements of Defect Generation during PVT Growth of SiC. Materials Science Forum, 2007, 556-557, 267-270.	0.3	6
57	&lt;i>In Situ&/i> Observation of Polytype Switches during SiC PVT Bulk Growth by High Energy X-Ray Diffraction. Materials Science Forum, 0, 615-617, 23-26.	0.3	6
58	Low temperature processing of hybrid nanoparticulate Indium Tin Oxide (ITO) polymer layers and application in large scale lighting devices. Thin Solid Films, 2011, 519, 5744-5747.	0.8	6
59	In-situ phase formation study of copper indium diselenide absorber layers from CuIn nanoparticles and evaporated selenium. Thin Solid Films, 2013, 535, 133-137.	0.8	6
60	Towards X-ray in&lt;i>situ&/i> visualization of ammonoothermal crystal growth of nitrides. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 1439-1442.	0.8	6
61	Limitations during Vapor Phase Growth of Bulk (100) 3C-SiC Using 3C-SiC-on-SiC Seeding Stacks. Materials, 2019, 12, 2353.	1.3	6
62	Intentional Incorporation and Tailoring of Point Defects during Sublimation Growth of Cubic Silicon Carbide by Variation of Process Parameters. Physica Status Solidi (B): Basic Research, 2020, 257, 1900286.	0.7	6
63	Overgrowth of Protrusion Defects during Sublimation Growth of Cubic Silicon Carbide Using Free-Standing Cubic Silicon Carbide Substrates. Crystal Growth and Design, 2021, 21, 4046-4054.	1.4	6
64	Determination of Exciton Capture Cross-Sections of Neutral Nitrogen Donor on Cubic and Hexagonal Sites in n-Type (N) 6H-SiC. Materials Science Forum, 2003, 433-436, 341-344.	0.3	5
65	Impact of Compensation on Optical Absorption Bands in the Below-Bandgap Region in n-Type (N) 6H-SiC. Materials Science Forum, 2003, 433-436, 333-336.	0.3	5
66	Growth of Phosphorous-Doped n-Type 6H-SiC Crystals using a Modified PVT Technique and Phosphine as Source. Materials Science Forum, 2004, 457-460, 727-730.	0.3	5
67	Electronic Raman Studies of Shallow Donors in Silicon Carbide. Materials Science Forum, 2006, 527-529, 579-584.	0.3	5
68	Depth-resolved and temperature dependent analysis of phase formation processes in Cu&lt;sup>2+</sup>Zn&lt;sup>2+</sup>Sn&lt;sup>2+</sup>Se films on ZnO substrates. Journal of Materials Science: Materials in Electronics, 2017, 28, 7730-7738.	1.1	5
69	Optimization of the SiC Powder Source Material for Improved Process Conditions During PVT Growth of SiC Boules. Materials, 2019, 12, 3272.	1.3	5
70	An adhesive bonding approach by hydrogen silsesquioxane for silicon carbide-based LED applications. Materials Science in Semiconductor Processing, 2019, 91, 9-12.	1.9	5
71	Investigation of the Growth Kinetics of SiC Crystals during Physical Vapor Transport Growth by the Application of In Situ 3D Computed Tomography Visualization. Advanced Engineering Materials, 2020, 22, 1900778.	1.6	5
72	Prospects of Bulk Growth of 3C-SiC Using Sublimation Growth. Materials Science Forum, 0, 1004, 113-119.	0.3	5

#	ARTICLE	IF	CITATIONS
73	Influence of the growth conditions on the formation of macro-steps on the growth interface of SiC-Crystals. Journal of Crystal Growth, 2021, 576, 126361.	0.7	5
74	On the Excitation Mechanism of Erbium and Ytterbium in the Quaternary Compounds InGaAsP. Materials Research Society Symposia Proceedings, 1996, 422, 255.	0.1	4
75	SiC Crystal Growth from the Vapor and Liquid Phase. Materials Research Society Symposia Proceedings, 2000, 640, 1.	0.1	4
76	Digital X-Ray Imaging of SiC PVT Process: Analysis of Crystal Growth and Powder Source Degradation. Materials Science Forum, 2000, 338-342, 71-74.	0.3	4
77	Photoluminescence Study of In-Situ Rare Earth Doped PVT-Grown SiC Single Crystals. Materials Science Forum, 2005, 483-485, 445-448.	0.3	4
78	Micro-Optical Characterization Study of Highly p-Type Doped SiC:Al Wafers. Materials Science Forum, 2005, 483-485, 393-396.	0.3	4
79	Basal Plane Dislocation Dynamics in Highly p-Type Doped versus Highly n-Type Doped SiC. Materials Science Forum, 2006, 527-529, 79-82.	0.3	4
80	Growth and Characterization of <sup>13</sup> C Enriched 4H-SiC for Fundamental Materials Studies. Materials Science Forum, 2007, 556-557, 13-16.	0.3	4
81	Modeling of the Mass Transport during Homo-Epitaxial Growth of Silicon Carbide by Fast Sublimation Epitaxy. Materials Science Forum, 2013, 740-742, 52-55.	0.3	4
82	Numerical reactive diffusion modeling of stacked elemental layer rapid thermal annealed chalcopyrite absorber layer formation. Thin Solid Films, 2015, 582, 397-400.	0.8	4
83	Comparison of Achievable Contrast Features in Computed Tomography Observing the Growth of a 4H-SiC Bulk Crystal. Materials, 2019, 12, 3652.	1.3	4
84	Characterization of protrusions and stacking faults in 3C-SiC grown by sublimation epitaxy using 3C-SiC-on-Si seeding layers. Advanced Materials Proceedings, 2021, 2, 774-778.	0.2	4
85	Fabrication of Bariumtrisulphide Thin Films as Precursors for Chalcogenide Perovskites. Physica Status Solidi (B): Basic Research, 2022, 259, .	0.7	4
86	Impact of SiC Source Material on Temperature Field and Vapor Transport During SiC PVT Crystal Growth Process. Materials Science Forum, 2001, 353-356, 11-14.	0.3	3
87	Aluminum Doping of 6H- and 4H-SiC with a Modified PVT Growth Method. Materials Science Forum, 2002, 389-393, 131-134.	0.3	3
88	On the Origin of the Below Band-Gap Absorption Bands in n-Type (N) 4H- and 6H-SiC. Materials Science Forum, 2004, 457-460, 645-648.	0.3	3
89	Progress and Limits of the Numerical Simulation of SiC Bulk and Epitaxy Growth Processes. Materials Science Forum, 2005, 483-485, 3-8.	0.3	3
90	Modeling and Experimental Verification of SiC M-PVT Bulk Crystal Growth. Materials Science Forum, 2006, 527-529, 75-78.	0.3	3

#	ARTICLE	IF	CITATIONS
91	Real-time Investigations on the Formation of $\text{CuIn}(\text{S,Se})_2$ while annealing precursors with varying sulfur content. Materials Research Society Symposia Proceedings, 2009, 1165, 1. Determination of material inhomogeneities in $\langle \text{mmi} \cdot \text{math} \text{ altimg= "si1.gif" display= "inline" overflow= "scroll" xmlns:xocs= "http://www.elsevier.com/xml/xocs/dtd" xmlns:xs= "http://www.w3.org/2001/XMLSchema" xmlns:xsi= "http://www.w3.org/2001/XMLSchema-instance" xmlns= "http://www.elsevier.com/xml/ja/dtd" xmlns:ja= "http://www.elsevier.com/xml/ja/dtd" xmlns:mml= "http://www.w3.org/1998/Math/MathML" xmlns:tb= "http://www.elsevier.com/xml/common/table/dtd" xmlns:sb= "http://www.elsevier.com/xml/co$	0.1	3
92	Step-Flow Growth of Fluorescent 4H-SiC Layers on 4 Degree Off-Axis Substrates. Materials Science Forum, 0, 740-742, 185-188.	1.8	3
93	Towards the Growth of SiGeC Epitaxial Layers for the Application in Si Solar Cells. Energy Procedia, 2015, 84, 236-241.	0.3	3
94	Solution Growth of Silicon Carbide Using the Vertical Bridgman Method. Crystal Research and Technology, 2018, 53, 1800019.	1.8	3
95	Modeling of the PVT Growth Process of Bulk 3C-SiC - Growth Process Development and Challenge of the Right Materials Data Base. Materials Science Forum, 0, 963, 157-160.	0.6	3
96	Large Area Growth of Cubic Silicon Carbide Using Close Space PVT by Application of Homoepitaxial Seeding. Materials Science Forum, 0, 1062, 74-78.	0.3	3
97	Review of Sublimation Growth of SiC Bulk Crystals. Materials Science Forum, 0, 1062, 104-112.	0.3	3
98	'Insitu Synthesis' of Source Material from Elemental Si and C during SiC PVT Growth Process and Characterization Using Digital X-Ray Imaging. Materials Science Forum, 2002, 389-393, 91-94.	0.3	3
99	Electrical and Optical Characterization of p-Type Boron-Doped 6H-SiC Bulk Crystals. Materials Science Forum, 2003, 433-436, 337-340.	0.3	2
100	Contactless Electrical Defect Characterization and Topography of a-Plane Grown Epitaxial Layers. Materials Science Forum, 2007, 556-557, 327-330.	0.3	2
101	Impact of n-Type versus p-Type Doping on Mechanical Properties and Dislocation Evolution during SiC Crystal Growth. Materials Science Forum, 2007, 556-557, 259-262.	0.3	2
102	Defect Etching of Non-Polar and Semi-Polar Faces in SiC. Materials Science Forum, 2007, 556-557, 243-246.	0.3	2
103	Bulk Growth of SiC. Materials Research Society Symposia Proceedings, 2008, 1069, 1.	0.1	2
104	Germanium Incorporation during PVT Bulk Growth of Silicon Carbide. Materials Science Forum, 2009, 615-617, 11-14.	0.3	2
105	Generation of Void-Like Structures during Hot-Hydrogen Etching of Si Substrates for 3C-SiC Epitaxy. Materials Science Forum, 0, 679-680, 127-130.	0.3	2
106	Optimising The Parameters For The Synthesis Of CuIn-Nanoparticles By Chemical Reduction Method For Chalcopyrite Thin Film Precursors. Materials Research Society Symposia Proceedings, 2013, 1538, 203-208.	0.1	2
107	Real-Time Measurement of the Evolution of Growth Facets during SiC PVT Bulk Growth Using 3-D X-Ray Computed Tomography. Materials Science Forum, 0, 778-780, 9-12.	0.3	2
108			

#	ARTICLE	IF	CITATIONS
109	Low temperature formation of CuIn <sub>1-x</sub> Ga <sub>x</sub> Se <sub>2</sub> solar cell absorbers by all printed multiple species nanoparticulate Se + Cu <sup>2+</sup> In + Cu <sup>2+</sup> Ga precursors. <i>Thin Solid Films</i> , 2015, 582, 60-68.	0.8	2
110	Characterization of kesterite thin films fabricated by rapid thermal processing of stacked elemental layers using spatially resolved cathodoluminescence. <i>Thin Solid Films</i> , 2015, 582, 387-391.	0.8	2
111	Annealing-Induced Changes in the Nature of Point Defects in Sublimation-Grown Cubic Silicon Carbide. <i>Materials</i> , 2019, 12, 2487.	1.3	2
112	Deep Electronic Levels in n-Type and p-Type 3C-SiC. <i>Materials Science Forum</i> , 0, 963, 297-300.	0.3	2
113	Vapor Growth of 3C-SiC Using the Transition Layer of 3C-SiC on Si CVD Templates. <i>Materials Science Forum</i> , 2019, 963, 149-152.	0.3	2
114	Optimization of the SiC powder source size distribution for the sublimation growth of long crystal boules. <i>Advanced Materials Proceedings</i> , 2021, 3, 540-543.	0.2	2
115	Chemical Vapor Deposition of 3C-SiC on [100] Oriented Silicon at Low Temperature &lt; 1200°C for Photonic Applications. <i>Materials Science Forum</i> , 0, 1062, 119-124.	0.3	2
116	Acceptor-Hydrogen Interaction in Ternary III-V Semiconductors. <i>Materials Science Forum</i> , 1995, 196-201, 987-992.	0.3	1
117	In-Situ Er-Doping of SiC Bulk Single Crystals. <i>Materials Science Forum</i> , 2004, 457-460, 723-726.	0.3	1
118	Influence of Growth Temperature on the Evolution of Dislocations during PVT Growth of Bulk SiC Single Crystals. <i>Materials Science Forum</i> , 2007, 556-557, 263-266.	0.3	1
119	Photoluminescence-Topography of the p-Type Doped SiC Wafers for Determination of Doping Inhomogeneity. <i>Materials Science Forum</i> , 2009, 615-617, 259-262.	0.3	1
120	P- and n-Type Doping in SiC Sublimation Epitaxy Using Highly Doped Substrates. <i>Materials Science Forum</i> , 2009, 615-617, 85-88.	0.3	1
121	Fundamental Study of the Temperature Ramp-Up Influence for 3C-SiC Hetero-Epitaxy on Silicon (100). <i>Materials Science Forum</i> , 0, 645-648, 151-154.	0.3	1
122	Efficient Image Segmentation for Detection of Dislocations in High Resolution Light Microscope Images of SiC Wafers. <i>Materials Science Forum</i> , 0, 679-680, 277-281.	0.3	1
123	Freestanding 3C-SiC Grown by Sublimation Epitaxy Using 3C-SiC Templates on Silicon. <i>Materials Science Forum</i> , 0, 717-720, 177-180.	0.3	1
124	Application of Printable ITO/PEDOT Nanocomposites as Transparent Electrodes in Optoelectronic Devices. , 2012, , .		1
125	Morphological and Optical Stability in Growth of Fluorescent SiC on Low Off-Axis Substrates. <i>Materials Science Forum</i> , 2013, 740-742, 19-22.	0.3	1
126	Application of 3-D X-Ray Computed Tomography for the &lt;i>In Situ&/i> Visualization of the SiC Crystal Growth Interface during PVT Bulk Growth. <i>Materials Science Forum</i> , 0, 740-742, 27-30.	0.3	1



#	ARTICLE	IF	CITATIONS
127	Lateral Boron Distribution in Polycrystalline SiC Source Materials. Materials Science Forum, 0, 740-742, 397-400.	0.3	1
128	Fabrication of Broadband Antireflective Sub-Wavelength Structures on Fluorescent SiC. Materials Science Forum, 0, 740-742, 1024-1027.	0.3	1
129	3C-SiC Bulk Sublimation Growth on CVD Hetero-Epitaxial Seeding Layers. Materials Science Forum, 0, 897, 15-18.	0.3	1
130	Growth, Defects and Doping of 3C-SiC on Hexagonal Polytypes. ECS Journal of Solid State Science and Technology, 2017, 6, P741-P745.	0.9	1
131	(Invited) Growth, Defects and Doping of 3C-SiC on Hexagonal Polytypes. ECS Transactions, 2017, 80, 107-115.	0.3	1
132	Vacuum-Free and Highly Dense Nanoparticle Based Low-Band-Gap CuInSe <sub>2</sub> Thin-Films Manufactured by Face-to-Face Annealing with Application of Uniaxial Mechanical Pressure. Coatings, 2019, 9, 484.	1.2	1
133	Optimization of the SiC Powder Source Size Distribution for the Sublimation Growth of Long Crystals Boules. Materials Science Forum, 2019, 963, 42-45.	0.3	1
134	Tracking of the Growth Interface during PVT-Growth of SiC Boules Using a X-Ray Computed Tomography Setup. Materials Science Forum, 0, 963, 14-17.	0.3	1
135	Advances in <i>In Situ</i> SiC Growth Analysis Using Cone Beam Computed Tomography. Materials Science Forum, 2019, 963, 5-9.	0.3	1
136	Determination of site occupancy of boron in 6H-SiC by multiple-wavelength neutron holography. Applied Physics Letters, 2022, 120, 132101.	1.5	1
137	<i>In Situ</i> Monitoring of Unintentionally Released Nitrogen Gas in the Initial PVT Silicon Carbide Growth Process Using Mass Spectrometry. Materials Science Forum, 0, 1062, 79-83.	0.3	1
138	Structural Defects in SiC Crystals Investigated by High Energy X-Ray Diffraction. Materials Science Forum, 2004, 457-460, 339-342.	0.3	0
139	Silicon Carbide Growth: C/Si Ratio Evaluation and Modeling. Materials Research Society Symposia Proceedings, 2006, 911, 2.	0.1	0
140	Defect Structures at the Silicon/3C-SiC Interface. Materials Science Forum, 0, 717-720, 423-426.	0.3	0
141	Photoluminescence Topography of Fluorescent SiC and its Corresponding Source Crystals. Materials Science Forum, 2013, 740-742, 421-424.	0.3	0
142	Microsecond Carrier Lifetimes in Bulk-Like 3C-SiC Grown by Sublimation Epitaxy. Materials Science Forum, 0, 740-742, 315-318.	0.3	0
143	Progress on Numerical Reactive Diffusion Modeling of CuInSe <sub>2</sub> Phase Formation for Solar Cell Applications. Energy Procedia, 2015, 84, 86-92.	1.8	0
144	Depth-resolved and temperature-dependent analysis of phase formation mechanisms in selenized Cu-Zn-Sn precursors by Raman spectroscopy. , 2016, , .		0

#	ARTICLE	IF	CITATIONS
145	Growth Conditions and <i>In Situ</i> Computed Tomography Analysis of Facetted Bulk Growth of SiC Boules. Materials Science Forum, 2018, 924, 245-248.	0.3	0
146	The 50th Anniversary of the German Association for Crystal Growth, DGKK. Crystal Research and Technology, 2020, 55, 2000009.	0.6	0
147	Analysis of Compositional Gradients in Cu(In,Ga)(S,Se) <sub>2</sub> Solar Cell Absorbers Using Energy Dispersive X-ray Analysis with Different Acceleration Energies. Materials, 2021, 14, 2861.	1.3	0
148	Special Equipment for Ammonothermal Processes. Springer Series in Materials Science, 2021, , 317-328.	0.4	0
149	Modeling and Experimental Verification of SiC M-PVT Bulk Crystal Growth. Materials Science Forum, 0, , 75-78.	0.3	0
150	Applicability of a Flat-Bed Birefringence Setup for the Determination of Threading Dislocations of Silicon Carbide Wafers. Materials Science Forum, 0, 1062, 113-118.	0.3	0